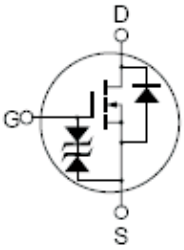
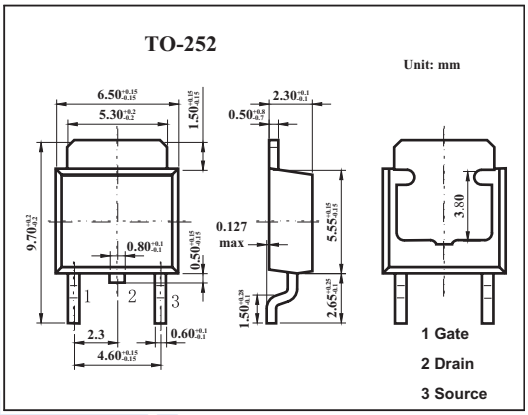
Silicon N-Channel MOSFET
2SK2735S

■ Features

- Low on-resistance
- R_{DS} = 20 mΩ typ.
- High speed switching
- 4V gate drive device can be driven from 5V source





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	20	A
	I_{dp} *	80	A
Power dissipation	P_D	20	W
Channel temperature	T_{ch}	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW≤10 μ s,Duty Cycle≤1%

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain source breakdown voltage	V_{DSS}	I_D=10mA,V_{GS}=0V	30			V
Drain cut-off current	I_{DSS}	V_{DS}=30V,V_{GS}=0			10	μ A
Gate leakage current	I_{GSS}	V_{GS}=±16V,V_{DS}=0			±10	μ A
Gate to source cutoff voltage	$V_{GS(off)}$	V_{DS}=10V,I_D=1mA	1.0		2.0	V
Forward transfer admittance	| Y_{fs} |	V_{DS}=10V,I_D=10A	8	16		S
Drain to source on-state resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=10A		20	28	mΩ
		V_{GS}=4V,I_D=10A		35	50	mΩ
Input capacitance	C_{iss}	V_{DS}=10V,V_{GS}=0,f=1MHZ		750		pF
Output capacitance	C_{oss}			520		pF
Reverse transfer capacitance	C_{rss}			210		pF
Turn-on delay time	t_{on}	I_D=10A,$V_{GS(on)}$=10V,RL=1Ω		16		ns
Rise time	t_r			225		ns
Turn-off delay time	t_{off}			85		ns
Fall time	t_f			90		ns